

N-Channel Enhancement Mode MOSFET

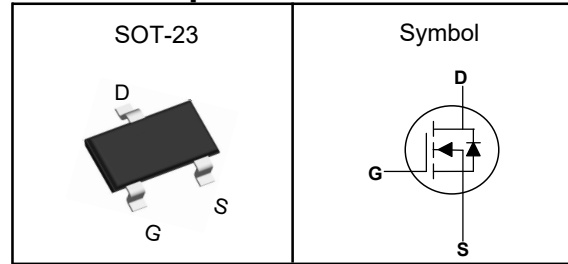
Features

- High Speed Power Switching
- Reliable and Rugged
- ROHS Compliant
- 100% Avalanche Tested

Applications

- Power Management in Desktop Computer
- DC/DC Converters

Pin Description



V_{DSS}	100	V
$R_{DS(ON)-Typ}$	95	m Ω
I_D	3.3	A

Absolute Maximum Ratings ($T_A=25^{\circ}C$, Unless Otherwise Noted)

Symbol	Parameter	Rating	Unit
V_{DSS}	Drain-Source Voltage	100	V
V_{GSS}	Gate-Source Voltage	± 20	V
T_J	Maximum Junction Temperature	-55 to 150	$^{\circ}C$
T_{STG}	Storage Temperature Range	-55 to 150	$^{\circ}C$
$I_{DM}^{①}$	Pulse Drain Current Tested	13.2	A
I_D	Continuous Drain Current	3.3	A
P_D	Maximum Power Dissipation	1.5	W

Thermal Characteristics

Symbol	Parameter	Rating	Unit
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	83.3	$^{\circ}C/W$

Note ① : Max. current is limited by bonding wire.

Note ② : UIS tested and pulse width are limited by maximum junction temperature 150 $^{\circ}C$.

Note ③ : Surface Mounted on 1in² FR-4 board with 1oz.



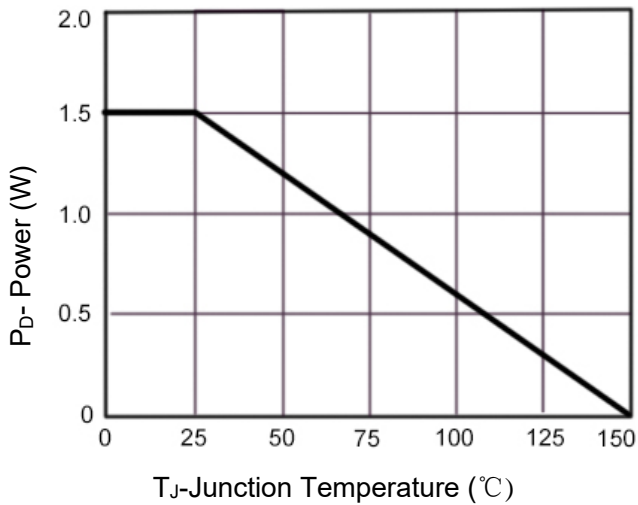
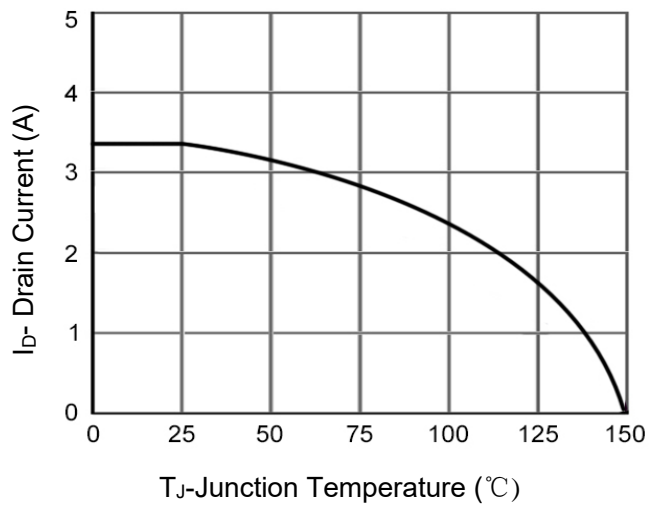
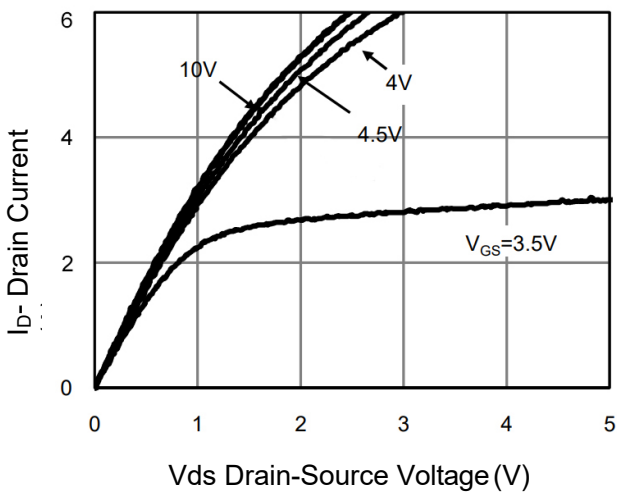
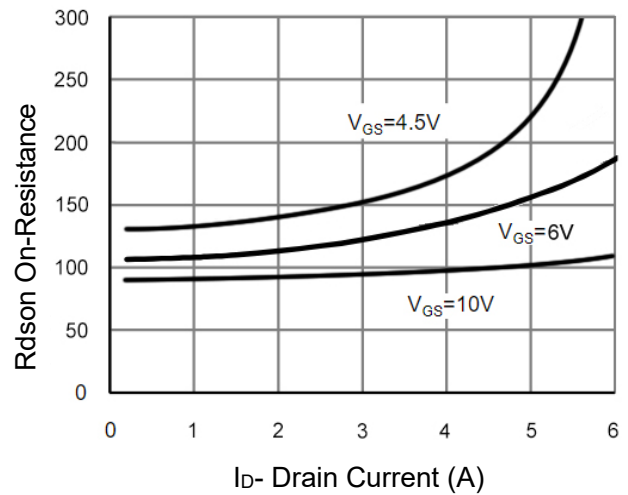
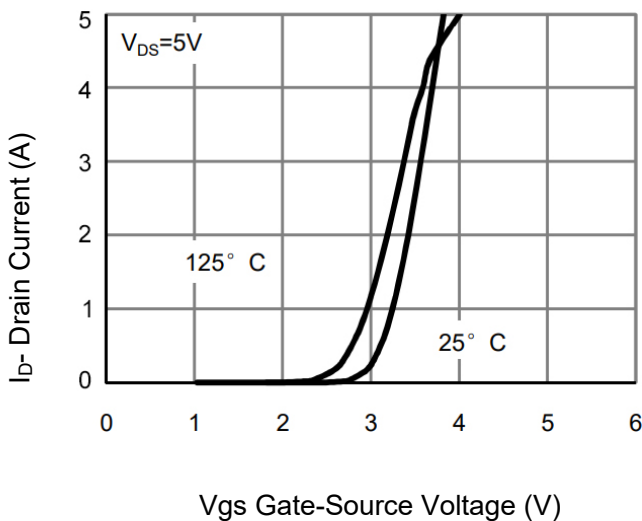
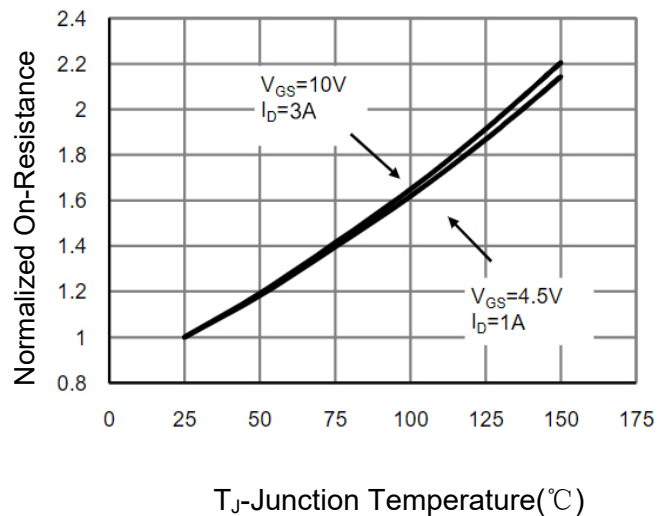
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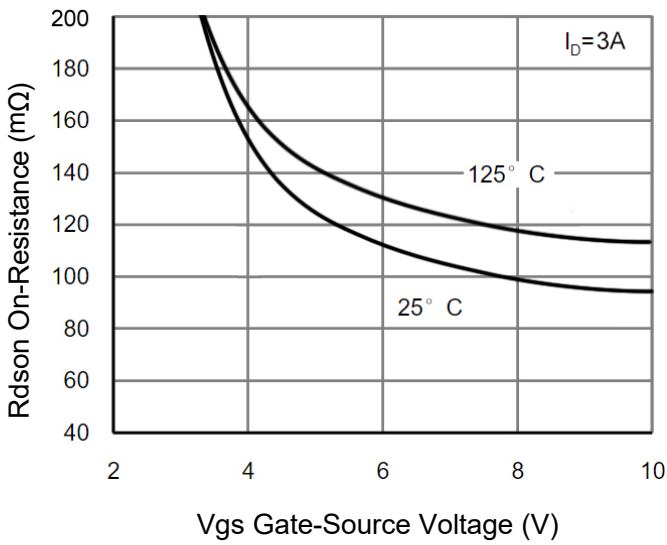
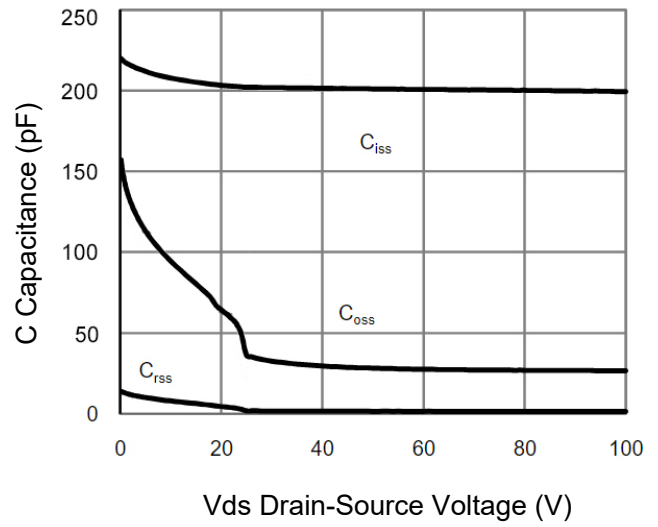
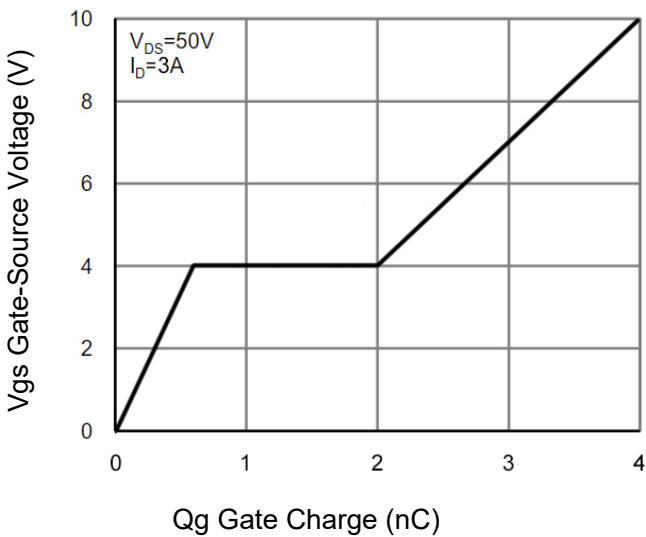
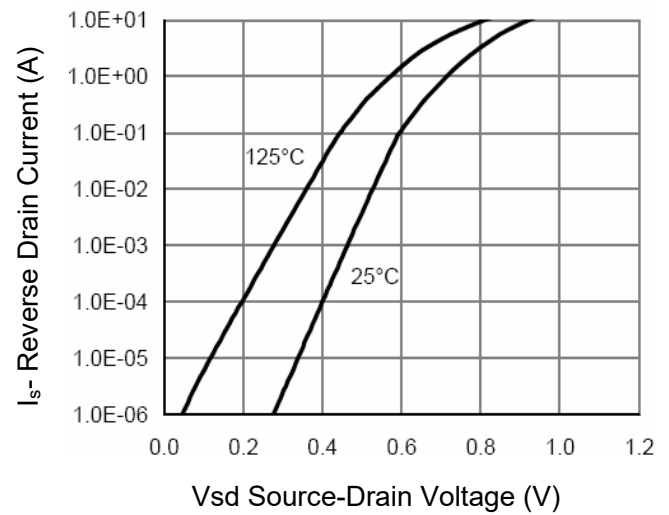
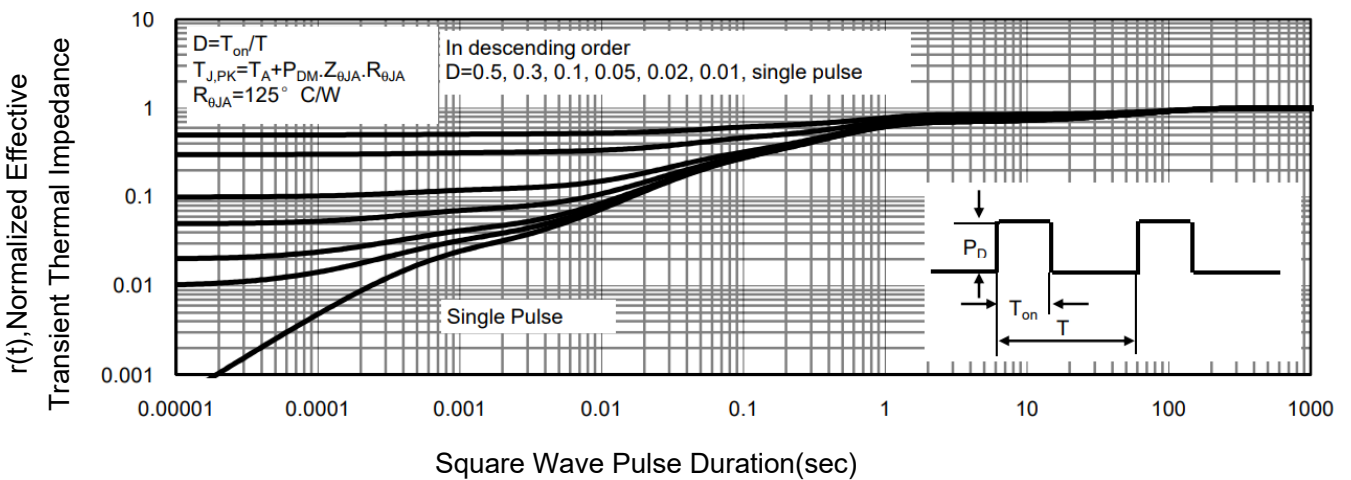
Electrical Characteristics ($T_J=25^{\circ}\text{C}$, Unless Otherwise Noted)

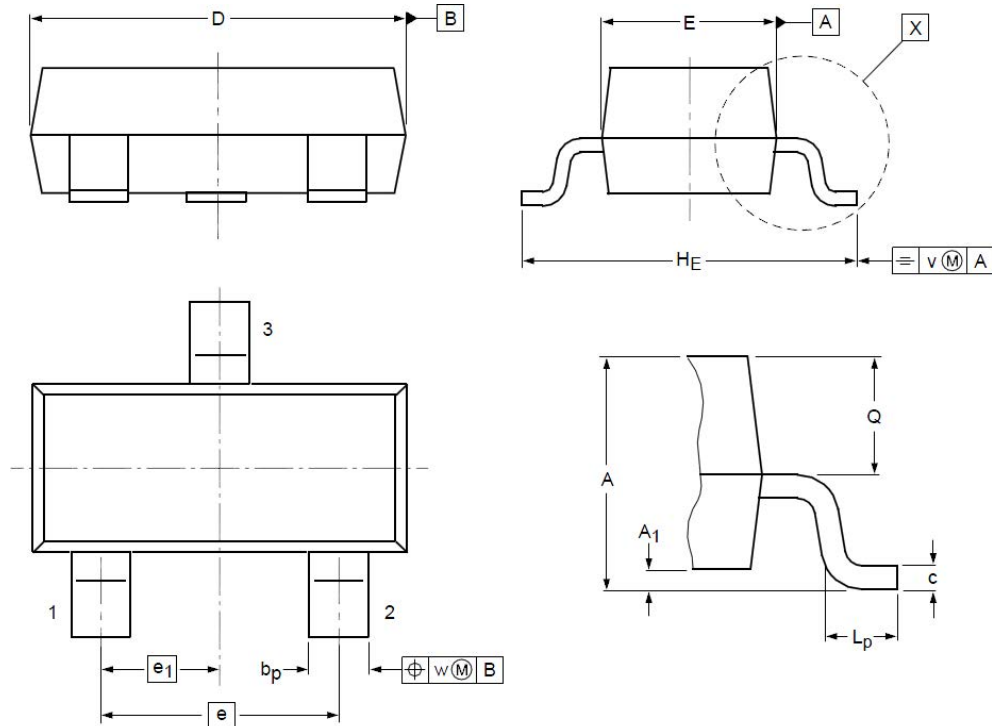
Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Static Electrical Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	100	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=100V, V_{GS}=0V$	---	---	1	μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	---	2.5	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
$R_{DS(on)}$	Drain-Source On-state Resistance	$V_{GS}=10V, I_D=3A$	---	95	130	$m\Omega$
		$V_{GS}=4.5V, I_D=1A$	---	135	190	$m\Omega$
Dynamic Characteristics ^⑤						
C_{iss}	Input Capacitance	$V_{DS}=50V, V_{GS}=0V, \text{Freq.}=1\text{MHz}$	---	200	---	pF
C_{oss}	Output Capacitance		---	30	---	
C_{rss}	Reverse Transfer Capacitance		---	2	---	
$T_{d(on)}$	Turn-on Delay Time	$V_{DD}=50V, V_{GS}=10V, I_D=3A, R_G=3\Omega$	---	12.5	---	nS
T_r	Turn-on Rise Time		---	19.5	---	
$T_{d(off)}$	Turn-off Delay Time		---	20	---	
T_f	Turn-off Fall Time		---	29	---	
Q_g	Total Gate Charge	$V_{DS}=50V, V_{GS}=10V, I_D=3A$	---	4	---	nC
Q_{gs}	Gate-Source Charge		---	0.6	---	
Q_{gd}	Gate-Drain Charge		---	1.4	---	
Source-Drain Characteristics						
V_{SD}	Diode Forward Voltage	$I_S=3A, V_{GS}=0V$	---	---	1.2	V

Note ④: Pulse test (pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$).

Note ⑤: Guaranteed by design, not subject to production testing.

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Typical Characteristics

Figure 1 Power De-rating

Figure 2 Drain Current

Figure 3 Output Characteristics

Figure 4 $R_{DS(on)}$ vs Drain Current

Figure 5 Transfer Characteristics

Figure 6 $R_{DS(on)}$ vs Junction Temperature

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Figure 7 Rdson vs Vgs

Figure 8 Capacitance vs Vds

Figure 9 Gate Charge

Figure 10 Source- Drain Diode Forward

Figure 11 Normalized Maximum Transient Thermal Impedance

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SOT23 Package Outline Dimensions


Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
A	0.90	1.05	1.20	e₁	--	0.95	--
A₁	0.01	0.05	0.10	H_E	2.10	2.40	2.50
b_p	0.38	0.42	0.48	L_p	0.40	0.50	0.60
c	0.09	0.13	0.15	Q	0.45	0.49	0.55
D	2.80	2.92	3.00	V	--	0.20	--
E	1.20	1.33	1.40	W	--	0.10	--
e	--	1.90	--				